

Th-PE-4

**Bias dependent shot noise in (Ga,Mn)As/GaAs Esaki diode**

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Th-PE-5

**Surface States in HgTe Quantum Well and Interface-Roughness Scattering.**

Alena A. Dobretsova<sup>1,2</sup>, Leonid S. Braginsky<sup>1,2</sup>, Matvey V. Entin<sup>1,2</sup>, Ze Don Kvon<sup>1,2</sup>, Nikolay N. Mikhailov<sup>1</sup>, and Sergey A. Dvoretzky<sup>1</sup>

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Th-PE-6

**Electronic structure of hydrogen adsorbed monolayer graphene on SiC studied by ARPES**

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Th-PE-7

**Cyclotron resonance in InGaAs Rashba bilayer systems**

Yasutaka Imanaka<sup>1</sup>, Kanji Takehana<sup>1</sup>, Shiro Hidaka<sup>2</sup>, Hyuma Iwase<sup>2</sup>, Masashi Akabori<sup>2</sup>, and Shoji Yamada<sup>2</sup>

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Th-PE-8

**Quantum dot driven it out of equilibrium: Measurement of the free energy**

Andrea Hofmann, Ville Maisi, Clemens Rössler, Julien Basset, Christian Reichl, Peter Märki, Werner Wegscheider, Thomas Ihn, and Klaus Ensslin

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Th-PE-9

**Extraordinary Absorption of Decorated Undoped Graphene**

Tobias Stauber<sup>1</sup>, Guillermo Gómez Santos<sup>2</sup>, and F. Javier García de Abajo<sup>3,4</sup>

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Th-PE-10

**Control of Tunnel Anisotropic Magnetoresistance by the Quantum Size Effect in GaMnAs Heterostructures**

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